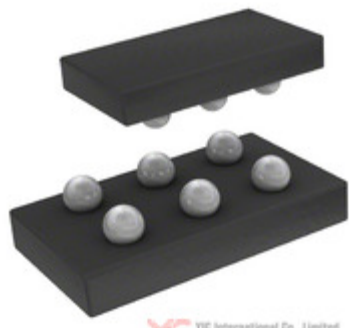

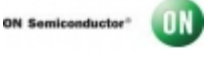
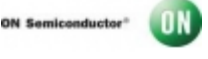

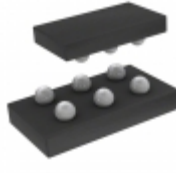
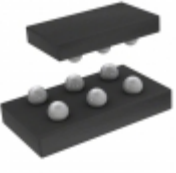
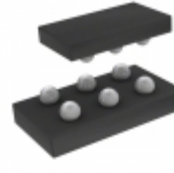
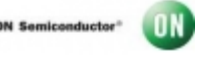
	<h2 style="color: red;">EFC6602R-A-TR</h2>
	Hersteller-Teilenummer: EFC6602R-A-TR
	Hersteller / Marke: AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung: MOSFET 2N-CH EFCP
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 4700 pcs Stock Available.
	Liefern von: Hong Kong
	Versandweg: DHL/Fedex/TNT/UPS/EMS
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	EFC6602R-A-TR
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET 2N-CH EFCP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	4700 pcs Stock
Serie	-
Betriebstemperatur	150 °C (TJ)
Befestigungsart	Surface Mount
Leistung - max	2W
Verpackung / Gehäuse	6-XFBGA
Supplier Device-Gehäuse	6-EFCP (2.7x1.81)
Typ FET	2 N-Channel (Dual) Common Drain
FET-Merkmal	Logic Level Gate, 2.5V Drive
Drain-Source-Spannung (Vdss)	-
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	-
Rds On (Max) @ Id, Vgs	-
VGS (th) (Max) @ Id	-
Gate Charge (Qg) (Max) @ Vgs	55nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)

EFC6602R-A-TR ist neu im Original, Suche EFC6602R-A-TR Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie EFC6602R-A-TR AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage EFC6602R-A-TR: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>EFC6605R-TR AMI Semiconductor / ON Semiconductor MOSFET 2N-CH EFCP</p>	 <p>EFC6604R-TR AMI Semiconductor / ON Semiconductor MOSFET 2N-CH EFCP</p>	 <p>EFC4630R-TR AMI Semiconductor / ON Semiconductor INTEGRATED CIRCUIT</p>	 <p>EFC4C012NLT DG AMI Semiconductor / ON Semiconductor NCH 30V 30A WLCSP6 DUAL</p>
 <p>EFC6602R-TR AMI Semiconductor / ON Semiconductor MOSFET 2N-CH EFCP</p>	 <p>EFC6601R-TR AMI Semiconductor / ON Semiconductor MOSFET 2N-CH EFCP</p>	 <p>EFC6601R-A-TR AMI Semiconductor / ON Semiconductor MOSFET 2N-CH EFCP</p>	 <p>EFC4C002NLT DG AMI Semiconductor / ON Semiconductor MOSFET 2 N-CHANNEL 8WLCSP</p>

heiße Teile

Mehr

⚙ EFC2J001NUZ	➔ EFC2J003MUZTCG-E2	➔ EFC2J003NUZTCG	D EFC2J004NUZTDG	➔ EFC4601-M-TR
⊣ EFC4601R-M-TR	⚙ EFC4601R-TR	D EFC4602-S-TR	➔ EFC4611-TR	➔ EFC4612R-S-TR
⚙ EFC4612R-TR	⊣ EFC4615R-TR	⚙ EFC4618R-P-TR	➔ EFC4618R-TR	➔ EFC4619R-TR
D EFC4621R-TR	⚙ EFC4622R-W-N	⊣ EFC4623R-TR	⚙ EFC4624R	➔ EFC4626R-TR
➔ EFC4627R-A-TR	➔ EFC4630R-TR	⚙ EFC4630R-TR	⊣ EFC6601R-TR	➔ EFC6602R-TR
➔ EFC6604R-TF	➔ EFC6605R-TR	D EFC6605R-V-TR	⚙ EFC6606R-TR	⊣ EFC6607R
⚙ EFC6611-A-TF	D EFC6611R-A-TF	➔ EFC6611R-A-TF	➔ EFC6611R-TF	➔ EFC6612R-A
⊣ EFC6612R-TF	⚙ EFC6617R-A-TF	➔ EFC6617R-TF	➔ EFC6617R-TF-ENG14	➔ EFC6618R-A
⚙ EFC6618R-TF	⊣ EFC8811R-TF	⚙ EFC8822R-TF	D EFCH1501TCB3	➔ EFCH1575PDB1
➔ EFCH1575TCA2	⚙ EFCH1575TDA1	⊣ EFCH1575TDB1	⚙ EFCH1747TDF1	➔ EFCH1765MTE3

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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